

Chapter 1

Quantum Wells in Photovoltaic Cells

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1.1 Introduction

The fundamental efficiency limit of a single bandgap solar cell is about 31% at one sun with a bandgap of about $E_g = 1.35$ eV [1], determined by the trade-off of maximising current with a smaller bandgap and voltage with a larger bandgap. Multiple bandgaps can be introduced to absorb the broad solar spectrum more efficiently. This can be realised in multi-junction cells, for example, where two or more cells are stacked on top of each other either mechanically or monolithically connected by a tunnel junction. An alternative – or complementary (see section 1.4) – approach is the quantum well cell (QWC).

1.2

(QWs) are thin layers of lower bandgap material in a host material with a higher bandgap. Early device designs placed the QWs in the doped regions of a p-n device [2], but superior carrier collection is achieved when an electric field is present across the QWs. More recent QWC designs have employed a p-i-n structure [3] with the QWs located in the intrinsic region; a schematic bandgap diagram is shown in figure 1.1. The carriers escape from the QWs thermally and by tunnelling [4, 5, 6].

The photocurrent is enhanced in a QWC compared to a cell made without QWs also known as barrier control, and experimentally it is observed that the voltage is enhanced compared with a bulk cell made of the QW material [7]. Hence QWCs can enhance the efficiency if the photocurrent enhancement is greater than the loss in voltage [8]. The potential for an

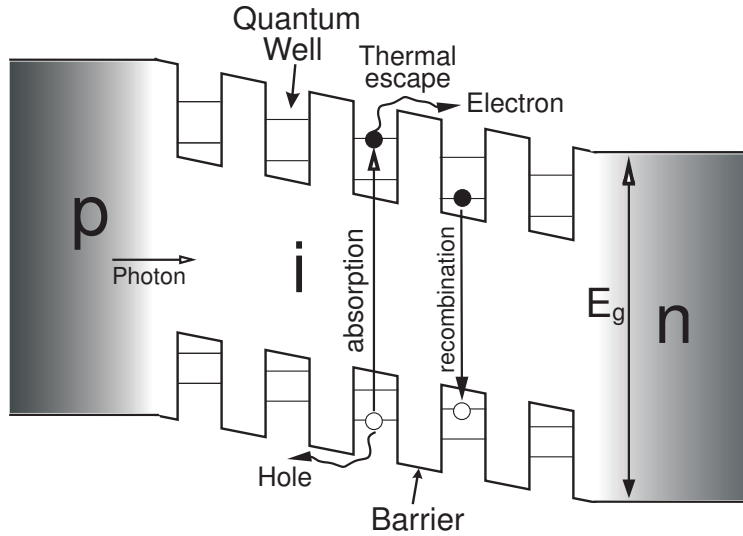


Figure 1.1. Schematic bandgap diagram of a Quantum Well Cell. The absorption threshold is determined by the lowest energy levels in the quantum wells. Carriers escape thermally assisted and by tunnelling.

efficiency enhancement is also discussed in references [9, 10]. The number of QWs is limited by the maximum thickness of the i-region maintaining an electric field across it. QWCs have been investigated quite extensively, both on GaAs as well as on InP substrates, and have been discussed in some detail also in references [11, 12].

Historically, the first p-i-n QWCs were in the material system AlGaAs/GaAs (barrier/well) on GaAs [13, 14, 15, 16, 17]. AlGaAs is closely lattice-matched to GaAs and the bandgap can be easily varied by changing the Al fraction (see figure 1.2) up to about 0.7 where the bandgap becomes indirect. However the material quality particularly that of AlGaAs is relatively poor because of contamination during the epitaxial growth, leading to a high number of recombination centres and hence a high dark current.

An alternative material to AlGaAs is InGaP which has better material quality, and an InGaP/GaAs QWC has been demonstrated [18]. However, the ideal single bandgap for a 1 sun solar spectrum is $E_g = 1.35$ eV, as indicated in figure 1.2, while GaAs has a bandgap of $E_g = 1.42$ eV and that of AlGaAs is still higher. The second material should therefore have a smaller bandgap than GaAs to absorb the longer wavelength light, keeping in mind that the quantum confinement raises the effective bandgap of the QWs.

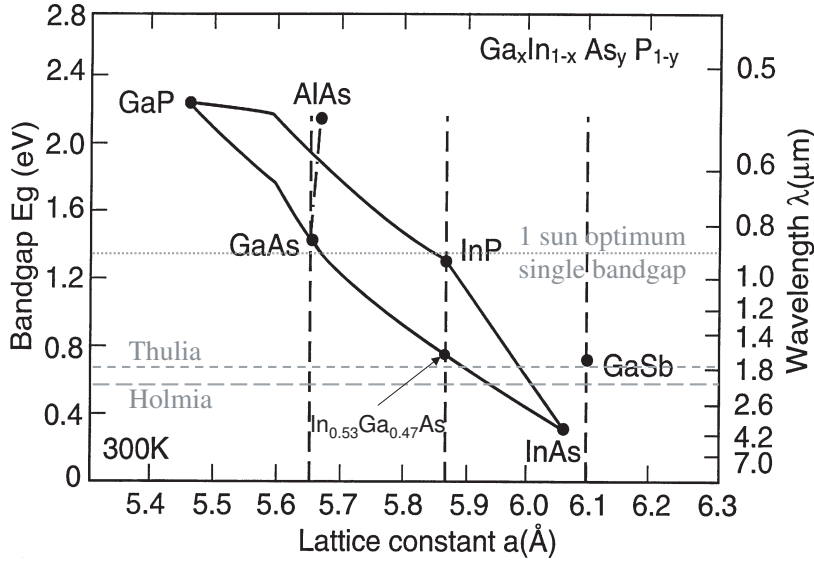


Figure 1.2. Lattice constant versus bandgap for $\text{In}_{1-x}\text{Ga}_x\text{As}_y\text{P}_{1-y}$ and AlGaAs compounds. Also indicated is the optimum bandgap for a single-bandgap PV cell under 1 sun, and the emission peaks of selective emitters Thulia and Holmia.

GaAs/InGaAs QWCs fulfil this criterion and they have been studied quite extensively [19, 20, 21, 22, 23, 24]. However, because InGaAs has a larger lattice constant than GaAs (see figure 1.2) it is strained. If the strain exceeds a critical value relaxation occurs at the top and bottom of the MQW stack, and the dislocations result in an increase in recombination and hence increased dark current [22]. This limitation means that strained GaAs/InGaAs QWCs cannot improve the efficiency compared to GaAs control cells [24].

Strain compensation techniques can be used to overcome this problem (see section 1.3), and QWCs in the material system GaAsP/InGaAs on GaAs have been investigated [25, 24, 26, 27, 28, 29]. These devices are also very suitable as bottom cells in a tandem configuration (see section 1.3).

QWCs based on InP are of interest for solar as well as for thermophotovoltaic (TPV) applications. First, material combinations such as InP/InGaAs were investigated [30, 31, 32, 6], which was then extended to quaternary material (lattice-matched to InP) $\text{InP}/\text{In}_{1-x}\text{Ga}_x\text{As}_y\text{P}_{1-y}$ ($x = 0.47y$) [33, 34, 35].

As in the GaAsP/InGaAs system on GaAs, strain compensation tech-

niques have been employed in $\text{In}_{1-x}\text{Ga}_x\text{As}/\text{In}_{1-z}\text{Ga}_z\text{As}$ QWCs on InP [36, 37, 38, 39, 40, 41].

QWCs have practical advantages due to both quantised energy levels and the greater flexibility of choice of materials. In particular, this allows engineering of the bandgap to better match the incident spectrum. The absorption threshold can be varied by changing the width of the QW and/or by changing its material composition.

This flexibility can be further increased by employing strain compensation techniques which are explained in more detail in Section section 1.3. In this way, longer wavelengths for absorption can be achieved than what is possible with lattice-matched bulk material, allowing optimisation of the bandgap.

The application of QWCs (based on InP) for thermophotovoltaics is discussed in section 1.6. For TPV applications the same concept of strain compensation can be applied to extend the absorption to longer wavelengths. This is important for relatively low temperature sources combined with appropriate selective emitters for example based on Holmia or Thulia.

Several studies indicate that QWCs have a better temperature dependence of efficiency than bulk cells [16, 42, 43, 44].

1.3 Strain compensation

In order to avoid strain relaxation, strain compensation techniques, first proposed by Matthews and Blakeslee [45], can be used to minimise the stress at the interface between the substrate and a repeat unit of two layers with different natural lattice constants. Layers with larger and smaller natural lattice constant compared to the substrate result in compressive and tensile strain respectively as shown in figure 1.3. When these two layers are strained against each other, the strain is compensated and the net force exerted on the adjacent layers is reduced. Therefore the build up of strain in a stack can be reduced, and hence its critical thickness is increased so that more such repeat units can be grown on top of each other without relaxation. If the strain compensation conditions are optimised to give zero stress at the interfaces between the repeat units, an unlimited number of periods can be grown in principle. In addition each individual layer has to remain below its critical thickness which means that this concept can only be used for thin layers such as quantum wells.

This technique is very suitable for multi quantum well structures; the barriers and wells are made of different materials with larger and smaller bandgaps but they can also have smaller and larger lattice constants (see figure 1.2), i.e. with tensile and compressive strain respectively (see figure 1.3 and figure 1.4). That means strained materials can be used for the quantum wells in order to reach lower bandgaps without compromising the

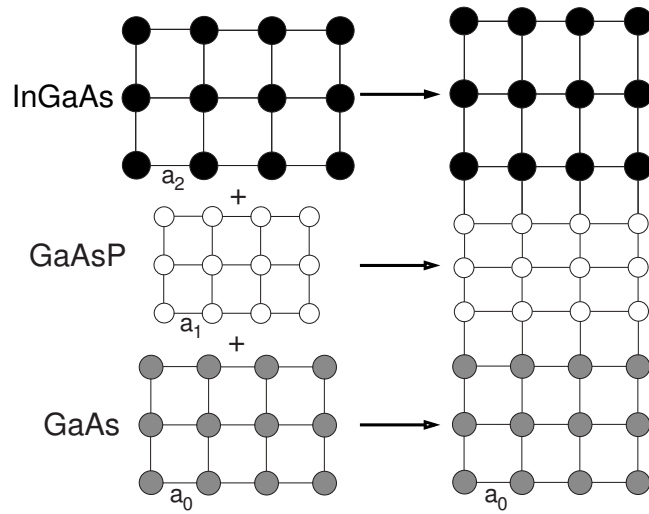


Figure 1.3. Schematic diagram of strain compensation: the natural lattice constant of GaAsP (a_1) is smaller than that of the GaAs substrate (a_0), and GaAsP barriers are therefore tensile strained, while the natural lattice constant of InGaAs (a_2) is larger, and hence InGaAs QWs are compressively strained.

quality of the device as dislocations are avoided. This technique, which extends the material range allowing further bandgap engineering, was first applied to photovoltaics in GaAsP/InGaAs QWCs [25].

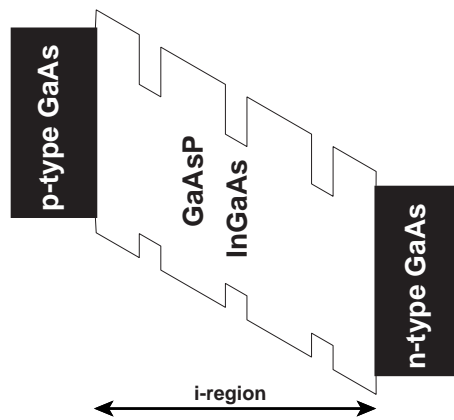


Figure 1.4. Bandgap diagram of a strain compensated QWC with InGaAs QWs and GaAsP barriers.

For highly strained layers the difference in elastic constants becomes

significant and it needs to be taken into account when considering the conditions for zero stress [46]. The strain for each layer i is

$$\epsilon_i = \frac{a_0 - a_i}{a_i} \quad (1.1)$$

where a_0 is the lattice constant of the substrate and a_i the natural lattice constant of layer i . The zero-stress strain-balance conditions are as follows:

$$\epsilon_1 t_1 A_1 a_2 + \epsilon_2 t_2 A_2 a_1 = 0 \quad (1.2)$$

$$a_0 = \frac{t_1 A_1 a_1 a_2^2 + t_2 A_2 a_2 a_1^2}{t_1 A_1 a_2^2 + t_2 A_2 a_1^2} \quad (1.3)$$

where $A = C_{11} + C_{12} - \frac{2C_{12}^2}{C_{11}}$ with elastic stiffness constants C_{11} and C_{12} , different for each layer, depending on the material.

The strain energy must be kept below a critical value, however, to avoid the onset of three-dimensional growth [47]. Lateral layer thickness modulations, particularly in the tensile strained material (i.e. barriers), are origins of dislocations and result in isolated highly defected regions if the elastic strain energy density reaches a critical value. In practice the strain balancing puts stringent requirements on growth.

1.4 QWs in Tandem Cells

In tandem cells two photovoltaic cells with two different bandgaps are stacked on top of each other. The bandgaps of the two cells can be optimised for the solar spectrum [48], and a contour plot of efficiency as a function of top and bottom cell bandgaps is shown in figure 1.5 for an AM0 spectrum. Tandem cells can be grown monolithically on a single substrate, connected with a tunnel junction. The top and bottom cell are connected in series, which means that the lower photocurrent of the two cells determines the current of the tandem device. Monolithic growth requires that the materials are lattice matched in order to avoid relaxation. A tandem with a GaInP top cell lattice matched to a GaAs bottom cell does not have the optimum bandgap combination as one can see in figure 1.5, and there is no good quality material available with a smaller bandgap than GaAs having the same lattice constant.

The standard approach to matching the currents in the GaInP/GaAs tandem is by thinning the top cell so that enough light is transmitted to the bottom cell to generate more current there [49]. This is not an optimum configuration, however, as the quantum efficiency of the top cell is reduced and in addition there are losses in the bottom cell due to more high-energy carriers relaxing to the bandedge.

It is possible to grow a virtual substrate, where the lattice constant is relaxed and the misfit dislocations are largely confined to electrically

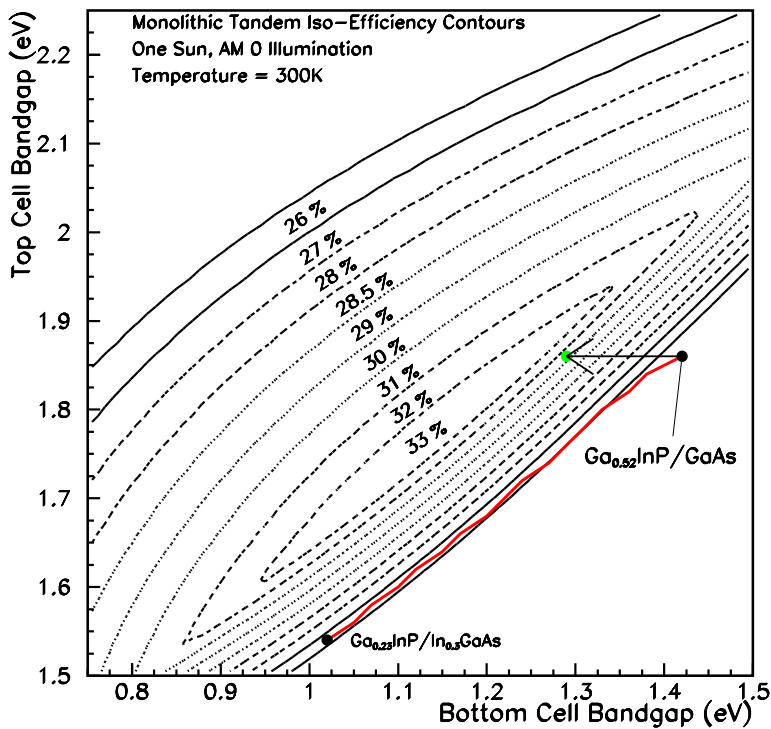


Figure 1.5. Contour plot of tandem cell efficiency as a function of top and bottom cell bandgaps.

inactive regions of the device. In this way the lattice constant can be changed before growing the tandem. But the bottom and top cell of the tandem should still be lattice matched with respect to each other and hence the combination of bandgaps is restricted indicated with a line in figure 1.5; the optimum where the currents in both cells are matched cannot be reached in general. Several groups have grown samples that fall on that line in figure 1.5 [50, 51].

QWs extend the absorption and therefore increase the photocurrent compared with a barrier control; hence a GaAs/InGaAs QWC generates more current than a GaAs cell and can be better matched to a GaInP top cell in a tandem cell under the solar spectrum [17, 23, 52, 53]. However, as mentioned in section 1.2, the voltage deteriorates due to the formation of misfit dislocations with increasing strain when incorporating strained

InGaAs QWs [22].

Strain compensated QWCs offer an attractive solution in that the link between lattice matching and bandgap is decoupled [24]. The bandgap of the bottom cell, for example, can be reduced with a strain compensated QWC, which means that one can move along a horizontal line in figure 1.5 improving the efficiency of a tandem cell quite rapidly [25]. QWCs for both the top and the bottom cell give an extra degree of freedom and optimisation of the bandgaps to obtain maximum efficiency becomes possible.

1.5 QWCs with light trapping

Not all the light is absorbed in the quantum wells because they are optically thin and their number limited. Hence light trapping techniques to increase the number of light passes through the MQW is desirable, boosting the QW photo-response significantly. The simplest form is a mirror on the back surface resulting in two light passes. Texturing the front or the back surface can further increase the path length of the light, in particular if the light is at a sufficiently large angle with respect to the normal so to obtain internal reflections. Another option is to incorporate gratings into the structure to diffract the light to large angles [54].

Light trapping is only desirable for the wavelength range where the optically thin QWs absorb. Other parts of the cell are optically thick and hence light trapping for photons with energies greater than the bandgap of the bulk material has a minimal effect if any. The energy of photons that are trapped but not absorbed (e.g. below bandgap photons) and additional high-energy carriers relaxing to the bandedge contribute to cell heating and are therefore undesirable.

A solution to this problem is to use a wavelength specific mirror such as a distributed Bragg reflector (DBR) [29]. A DBR consists of alternating layers of high and low refractive index material, each one-quarter of a wavelength thick. Constructive interference occurs for the reflected light of the design wavelength and adding periods to the DBR causes a higher reflection due to the presence of more in-phase reflections from the added interfaces. DBRs maintain a high reflectance within a region around the design wavelength known as the stop-band. As the refractive index contrast between the two materials in the DBR increases, the peak reflection rises and the stop-band widens.

This technique is particularly attractive for multi-junction cells where the second cell is a QWC with a DBR on an active Ge substrate. In figure 1.6 the quantum efficiency of a typical QWC with 20 QW is shown with and without a 20.5 period DBR, as well as the reflectance of the DBR; the sample description of the QWC with DBR is given in table 1.1. The quantum efficiency (QE) of the QWC with DBR in figure 1.6 is calculated

from the measured QE and the calculated DBR reflectance. The DBR reflects back only the relevant wavelength range that can be absorbed in the MQW, significantly boosting its spectral response.

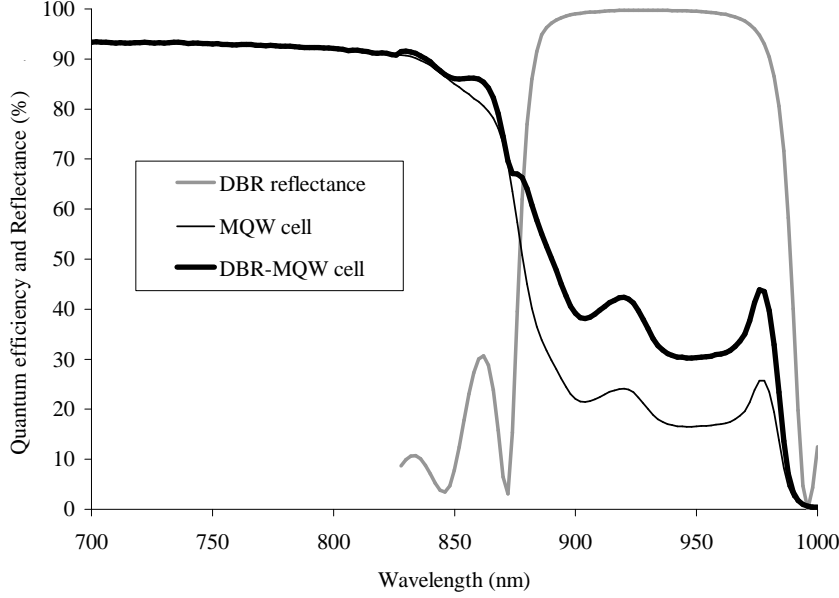


Figure 1.6. Quantum efficiency of a 20 QW device with and without DBR, and reflectance of the DBR.

As the stop-band of the DBR can be made quite abrupt, most longer wavelength light is allowed through, so that an active Ge substrate as a third junction can be employed, which would still produce more than 200 A/m^2 , more than enough photocurrent compared with the other two junctions (see below). The transmission through to a Ge substrate of a tandem cell with a GaInP top cell and a QWC with DBR as bottom cell has been modelled with a multi-layer programme and is shown in figure 1.7 compared with a tandem having a GaAs p-n junction as a bottom cell. As one can see the transmission of photons of energy below the bandgap of the bottom cell is similarly high in both cases.

In table 1.2 the short-circuit current density J_{sc} for AM0 illumination is shown for this QWC (20 QWs) with and without a 20.5 period DBR, compared with a p-n control cell [29]. In a tandem configuration, assuming a cut-off wavelength of 650 nm, corresponding to the bandgap of a GaInP top cell, the p-n control cell is expected to have a typical J_{sc} of 158 A/m^2 . Introducing a QWC with DBR improves J_{sc} by 16% to 183 A/m^2 , which is much better current matched to the GaInP top cell. A commercial triple-junction cell with GaInP top cell, a standard p-n GaAs junction and

Table 1.1. Sample description of QWC with DBR.

Layer	Repeats	Material	Thickness (\AA)	Doping	Conc. (cm^{-3})
Cap	1	GaAs	2200	p	2×10^{19}
Window	1	$\text{Al}_{0.8}\text{GaAs}$	450	p	1×10^{18}
Emitter	1	GaAs	5000	p	2×10^{18}
i-region	1	GaAs	100		
$\frac{1}{2}$ barrier	20	$\text{GaAsP}_{0.06}$	210		
QW	20	$\text{In}_{0.17}\text{GaAs}$	70		
$\frac{1}{2}$ barrier	20	$\text{GaAsP}_{0.06}$	210		
i-region	1	GaAs	100		
Base	1	GaAs	24000	n	1.5×10^{17}
DBR	20	$\text{Al}_{0.5}\text{GaAs}$	144	n	1×10^{18}
DBR	20	AlAs	538	n	1×10^{18}
DBR	20	$\text{Al}_{0.5}\text{GaAs}$	144	n	1×10^{18}
DBR	20	$\text{Al}_{0.13}\text{GaAs}$	520	n	1×10^{18}
DBR	1	$\text{Al}_{0.5}\text{GaAs}$	144	n	1×10^{18}
DBR	1	AlAs	538	n	1×10^{18}
DBR	1	$\text{Al}_{0.5}\text{GaAs}$	144	n	1×10^{18}
Buffer	1	GaAs	1000	n	1.5×10^{18}
Substrate		GaAs		n	

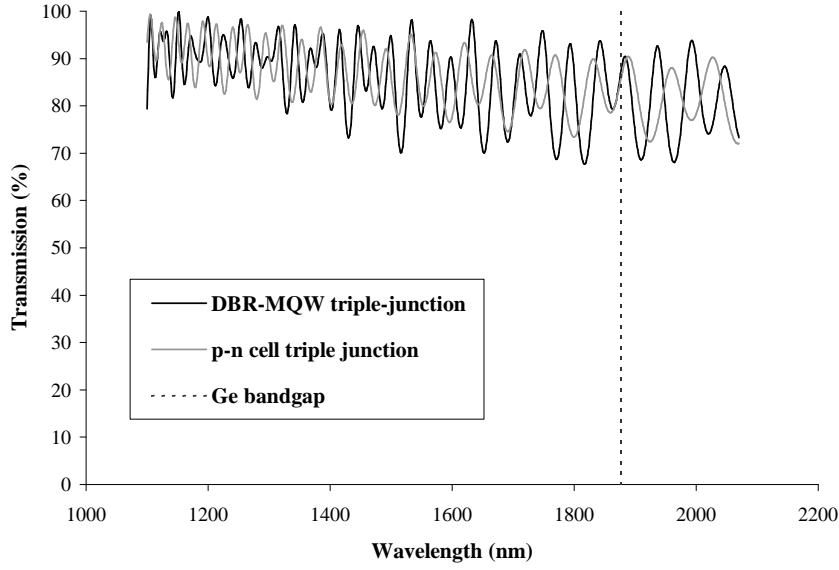


Figure 1.7. Calculated transmission through to a Ge substrate of a tandem cell with a GaInP top cell and as bottom cell a QWC with DBR, compared with a tandem with a GaAs p-n bottom cell.

an active Ge substrate has an AM0 efficiency of 26.0% [55]; if the GaAs junction is replaced with a QWC with DBR the efficiency is calculated to improve by about 3.4 percentage points or 13% to 29.4%.

Table 1.2. Short-circuit current densities J_{sc} and efficiencies for AM0 illumination. The tandem J_{sc} assumes a cut-off wavelength of 650 nm. The QWC has 20 QWs and the DBR 20.5 periods. The triple-junction efficiencies are based on a device with a GaInP top cell and an active Ge substrate.

Cell type	J_{sc} (A/m ²)	Tandem J_{sc} (A/m ²)	Triple-junction efficiency
QWC with DBR	339	183	29.4%
QWC without DBR	330	171	
p-n control	320	158	26.0% [55]

1.6 QWCs for Thermophotovoltaics

Thermophotovoltaics (TPV) is the same principle as photovoltaics but the source is at a lower temperature than the sun, typically around 1500-2000 K instead of 6000 K, and much closer. In TPV applications often a combustion process is used as heat source (e.g. using fossil fuels or biomass), but other heat sources such as nuclear, indirect solar or industrial high-grade waste heat can be used too. Because the source has a lower temperature in TPV, lower bandgap materials are required to absorb the (near-)infrared light more efficiently. Often a selective emitter is introduced between the source and the photovoltaic cells to obtain a narrow band as opposed to a broad black or grey-body spectrum, increasing the cell conversion efficiency. TPV is described in more detail for example in references [56, 57].

QWCs have advantages for TPV applications, and substantial progress has been made in the development of QWCs for TPV focusing on InP-based materials [58]. QWCs were first introduced for TPV applications independently by Griffin et al [32] and Freundlich et al [59]. These InGaAs/InP QWCs indicated better performance than InGaAs bulk cells, for example enhancing V_{oc} and improved temperature dependence. These are important parameters in TPV, as the cells are very close to a hot source, and the power densities are high giving rise to higher currents which may pose series resistance problems. Further development of QWCs has been in the quaternary system $\text{In}_{1-x}\text{Ga}_x\text{As}_y\text{P}_{1-y}$ lattice-matched to InP ($x = 0.47y$), with very good material quality, and which can be optimised for a rare-earth selective emitter Erbium having a peak emission of about 1.5 μm , for

example, but which is also attractive for hybrid solar-TPV applications [34].

Many TPV systems operate at temperatures more suitable for longer wavelength selective emitters such as Thulia and Holmia with peak emissions of about 1.7 and 1.95 μm respectively. However, the smallest bandgap achievable with lattice-matched material on InP is that of $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ with an absorption edge of about 1.7 μm (see figure 1.2.) Strain-compensation techniques can be employed to extend the absorption, which are unique to QWCs [36].

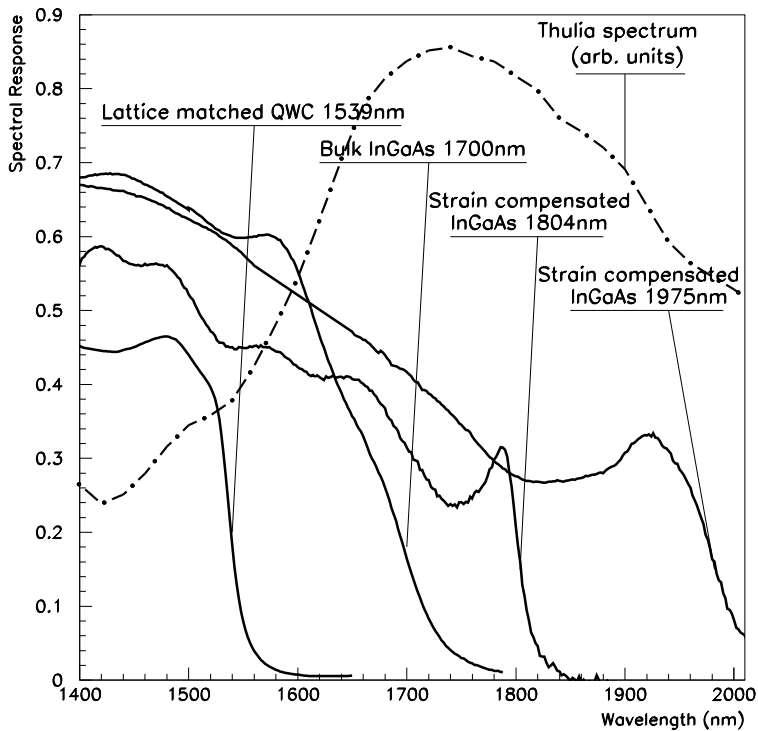


Figure 1.8. Experimental external quantum efficiency of TPV QWC devices (plus a bulk $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ device) with successively longer absorption, including a Thulia spectrum (arbitrary units).

$\text{In}_{1-x}\text{Ga}_x\text{As}/\text{In}_{1-z}\text{Ga}_z\text{As}$ strain-compensated QWCs have been shown to extend the absorption (see figure 1.8) while retaining a dark current similar to an $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ bulk cell, and lower than that of a GaSb cell

with similar bandgap (see figure 1.9) [37, 39]. A 40 QW $\text{In}_{1-x}\text{Ga}_x\text{As}/\text{In}_{1-z}\text{Ga}_z\text{As}$ strain-compensated QWC was designed for a Thulia emitter [41], absorbing out to $1.97 \mu\text{m}$ as shown in figure 1.8. Absorption beyond $2 \mu\text{m}$ has been achieved with a 2 QW cell, although in this case the collection efficiency was incomplete except at high temperatures and reverse bias [38].

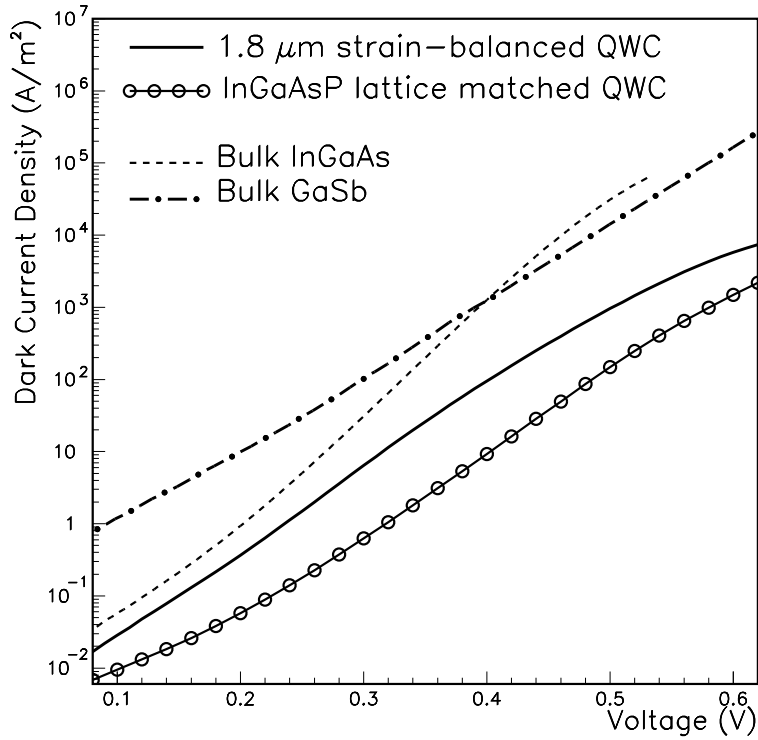


Figure 1.9. Dark current densities of TPV cells.

A mirror at the back can significantly increase the contribution of the QWs as discussed in section 1.5. Back reflection is particularly important as a form of spectral control in a TPV system, as below-bandgap photons are reflected back to the source increasing the system efficiency. We observe a back reflectivity of about 65% just from a standard gold back contact [39].

As an alternative, Si/SiGe QWCs were grown for TPV applications, but the absorption of the SiGe QWs is very low [60].

1.7 Conclusions

The primary advantage of incorporating quantum wells in photovoltaic cells is the flexibility offered by bandgap engineering by varying QW width and composition. The use of strain-compensation further increases this flexibility by extending the range of materials and compositions that can be employed to achieve absorption thresholds at lattice constants that do not exist in bulk material. In a tandem or multi-junction configuration QWCs allow current matching and optimising the bandgaps for higher efficiencies.

Light trapping schemes are an important technique to boost the quantum efficiency in the QWs. DBRs are particularly suited for QWCs in multi-junction devices, allowing light transmission to the lower bandgap junctions underneath.

The flexibility of materials, in particular with strain compensation, combined with the enhanced performance of QWCs make them especially suitable for TPV. QWCs are unique in that the absorption can be extended to wavelengths unattainable for lattice-matched bulk cells, while retaining a similar dark current. Strain-compensated QWCs can be optimised for long-wavelength selective emitters such as Thulia.

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